

- L14: (221458) 12 near 3
- L15: (16832) 13 with 14
- L16: (1132) 15 with 8
- L17: (781446) etch\$4 resist
- L18: (223) 16 and 17
- L19: (68) 18 and 11
- L20: (37845) different adj height
- L21: (55188) different adj (height depth)
- L22: (11) 11 near 2 21
- L23: (20) Backward citation search 1
- L24: (0) Forward citation search 1
- L25: (10) Backward citation search 2
- L26: (1) Forward citation search 2
- L27: (7) Backward citation search 3
- L28: (88) 19 23 25 27
- L29: (2) "20020016041"
- L30: (2) 09/902243
- L31: (907735) gate
- L32: (2782086) dielectric insulat\$4 oxide
- L33: (113289) 31 adj 32
- L34: (228007) thicker different adj thickness
- L35: (4681) 33 near 6 34
- L36: (6) 28 and 35
- L37: (4263) 5 with 10
- L38: (22) 35 with 37
- L39: (1) "RRAR001" PM

DSs US-PGPUB, USPAT, EPO, JPO, DERWENT, ISM, TDB

Default operator: OR

Plurals

Highlight all hit terms initially

19 23 25 27

Dec. 2004

DS form ISAR form Image Text HTML

	U	Inventor	Document	Issue	P	Title	Current	Current XR	Retrieval	S	C	P	Image	Doc	P
1		Kunikiyo, Tai	US 6762477	2004:4		Semiconductor device	257/506	257/398						US 676247	
2		Saito, Kenji	US 6596608	2003:3		Method of manufacturing non-volatile semico	438/424	257/E21.68						US 659660	
3		Maeda, Shige	US 6314021	2001:4		Nonvolatile semiconductor memory device a	365/185	257/314						US 631402	
4		Haskell, Jacob	US 4495025	1985:1		Process for forming grooves having different	438/427	257/510						US 449502	
5		Kim, Sun-You	US 2004018	2004:1		Self-aligned trench isolation method and sem	257/374							US 200401	
6		Kim, Sun-You	US 2004021	2004:1		Nonvolatile memory device having STI struct	257/315							US 200402	
7		Tanaka, Yosh	US 2004018	2004:9		Semiconductor device comprising capacitor	438/257	257/E21.64						US 200401	
8		Yuan, Jack H.	US 2004017	2004:2		Scalable self-aligned dual floating gate memo	438/257	257/E21.88						US 200401	
9		Oh, Jae-Hee	US 2004017	2004:2		Semiconductor device and method of manufa	257/303							US 200401	
10		Lee, Sang-Eu	US 2004015	2004:4		Method of manufacturing a semiconductor in	257/331							US 200401	

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